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63. (New) The device of claim 61, wherein the silicon-containing precursor layer is selected from the group comprising hexamethyldisilazane, tetramethyldisilazane, octamethylcyclotetrasilazane, hexamethylcyclotrisilazane, diethylaminotrimethylsilane and dimethylaminotrimethylsilane.
64. (New) The device of claim 61, wherein the silicon-containing precursor layer comprises a silane.
65. (New) A device having a precursor layer comprising:
- a silicon substrate including at least one semiconductor layer;
 - a precursor layer comprising a metal-free silicon-containing material formed over at least a portion of said silicon substrate.
66. (New) A semiconductor device having a precursor layer comprising:
- a substrate including at least one semiconductor layer; and
 - a precursor layer comprising a metal-free silicon-containing material from a silazane source formed over at least a portion of said at least one semiconductor layer.
67. (New) A semiconductor device having a precursor layer containing no metal comprising:
- a silicon substrate including at least one semiconductor layer; and
 - a precursor layer comprising a metal-form silicon-containing material from a silane source formed over at least a portion of said silicon substrate.
68. (New) A semiconductor device having a precursor layer comprising:
- a substrate having at least one semiconductor layer;
 - a transistor structure formed proximate to said substrate, said transistor structure including
 - a source formed in said substrate,
 - a drain formed in said substrate, and

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a gate oxide layer formed over an active area between said source and drain; and

a precursor layer comprising a metal-free silicon-containing material formed over at least a portion of the transistor structure.

69. (New) The device of claim 68, wherein a gate electrode is formed over said barrier layer.

70. (New) The device of claim 68, wherein said gate electrode is doped with phosphor.

71. (New) The device of claim 68, wherein said gate electrode is doped with boron.

72. (New) A capacitor device comprising:

an electrode formed over a substrate; and

a precursor layer comprising a metal-free silicon-containing material formed over the electrode.

73. (New) A capacitor device comprising:

an electrode formed over a substrate; and

a precursor layer comprising a metal-free silicon-containing material from a silazane source formed over the electrode.

74. (New) A capacitor device comprising:

an electrode formed over a substrate; and

a precursor layer comprising a metal-free silicon-containing material from a silane source formed over the electrode.

REMARKS

New claims 61-74 have been added. All of the claims recite, or ultimately depend from claims that recite, a precursor layer comprising a metal-free silicon-containing